Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
20V	0.4Ω @ V_{GS} = 4.5V	1A
	0.7Ω @ V_{GS} = 1.8V	0.8A

Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage $V_{GS(TH)}$, 1.0V Max.
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surfaced Mount Package
- Ultra-Low Package Profile, 0.4mm Maximum Package Height
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

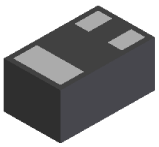
This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions

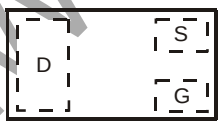
Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.001 grams (Approximate)

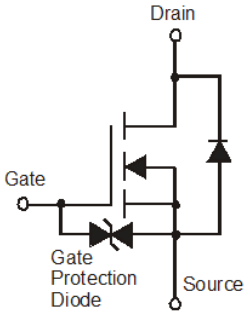
X2-DFN1006-3



Bottom View



Top View
Internal Schematic



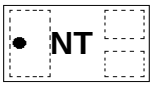
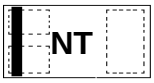
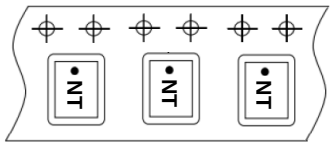
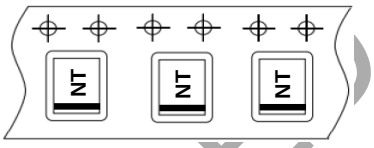
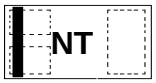
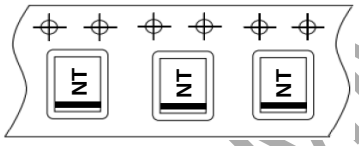
EQUIVALENT CIRCUIT

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2500UFB4-7	X2-DFN1006-3	3,000/Tape & Reel
DMN2500UFB4-7B	X2-DFN1006-3	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

DMN2500UFB4-7	 Top View Dot Denotes Drain Side From date code 1527 (YYWW), this changes to:  Top View Bar Denotes Gate and Source Side  
DMN2500UFB4-7B	 Top View Bar Denotes Gate and Source Side NT = Part Marking Code 

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±6	V
Continuous Drain Current (Note 5) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	810 640	mA
	t<10s	T_A = +25°C T_A = +70°C	I_D	950 750	mA
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	1000 800	mA
	t<10s	T_A = +25°C T_A = +70°C	I_D	1200 1000	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	4	A
Maximum Body Diode Continuous Current			I_S	850	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.46	W
	T_A = +70°C		0.29	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	279	°C/W
	t<10s		210	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	0.95	W
	T_A = +70°C		0.6	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	134	°C/W
	t<10s		100	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	-	-	100	nA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±1.0	µA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	-	1.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	0.3	0.4	Ω	V_{GS} = 4.5V, I_D = 600mA
			0.4	0.5		V_{GS} = 2.5V, I_D = 500mA
			0.5	0.7		V_{GS} = 1.8V, I_D = 350mA
Forward Transfer Admittance	$\|Y_{fs}\|$	-	1.4	-	S	V_{DS} = 10V, I_D = 400mA
Diode Forward Voltage	V_{SD}	-	0.7	1.2	V	V_{GS} = 0V, I_S = 150mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	60.67	-	pF	V_{DS} =16V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	9.68	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	5.37	-	pF	
Gate Resistance	R_g	-	93	-	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	-	736.6	-	pC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA
Gate-Source Charge	Q_{gs}	-	93.6	-	pC	
Gate-Drain Charge	Q_{gd}	-	116.6	-	pC	
Turn-On Delay Time	$t_{D(ON)}$	-	5.1	-	ns	V_{DD} = 10V, V_{GS} = 4.5V, R_L = 47Ω, R_G = 10Ω, I_D = 200mA
Turn-On Rise Time	t_R	-	7.4	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	26.7	-	ns	
Turn-Off Fall Time	t_F	-	12.3	-	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

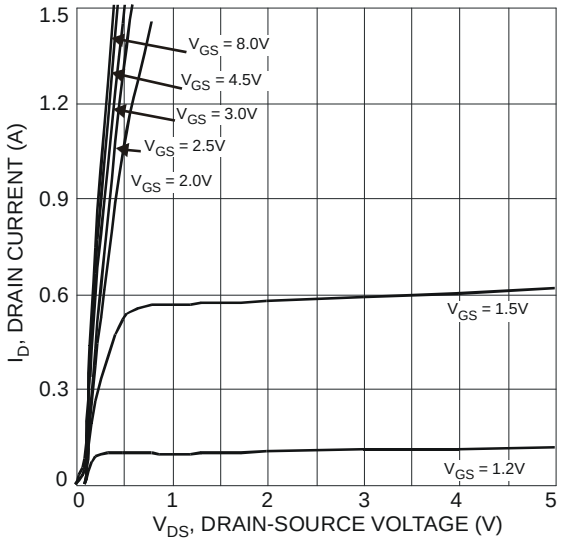


Fig. 1 Typical Output Characteristics

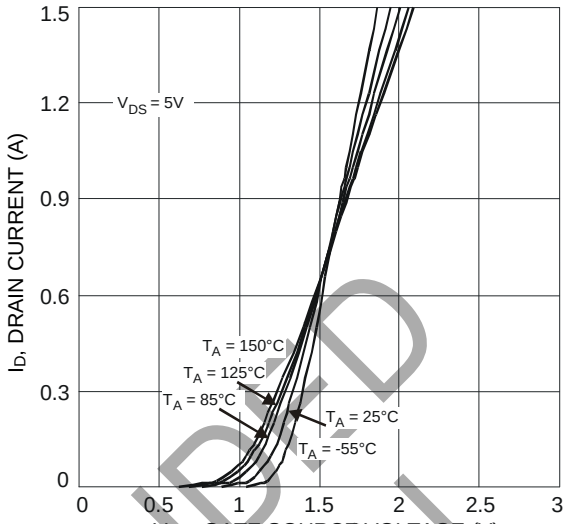


Fig. 2 Typical Transfer Characteristics

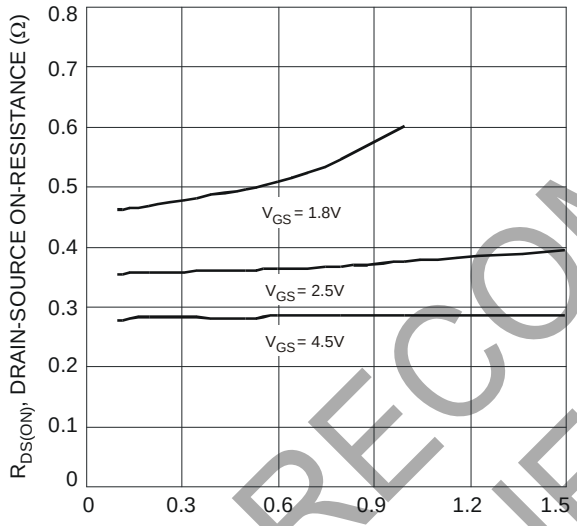


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

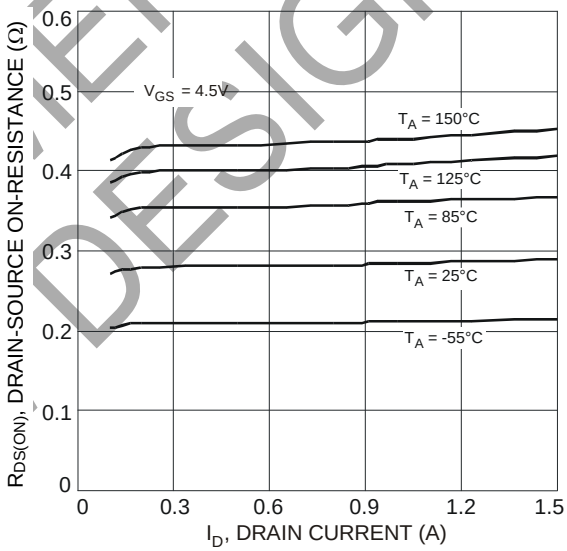


Fig. 4 Typical Drain-Source On-Resistance
vs. Drain Current and Temperature

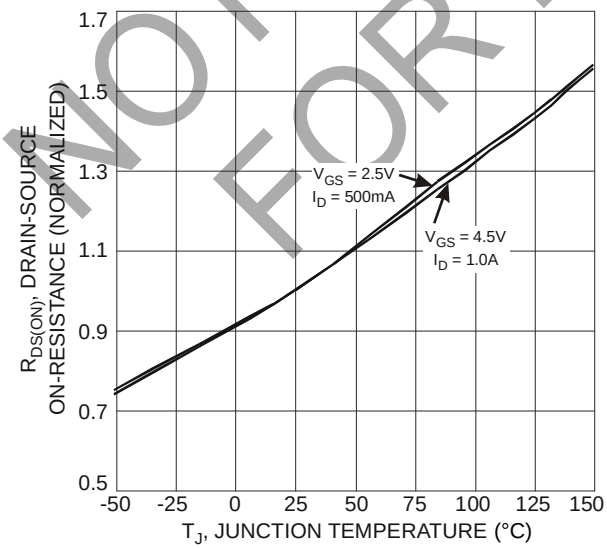


Fig. 5 On-Resistance Variation with Temperature

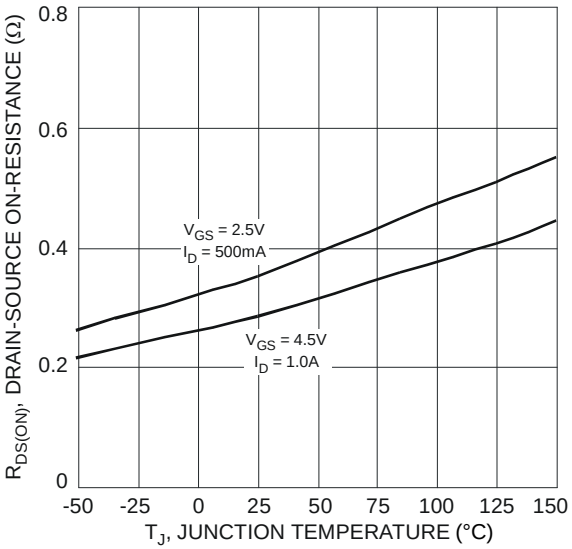


Fig. 6 On-Resistance Variation with Temperature

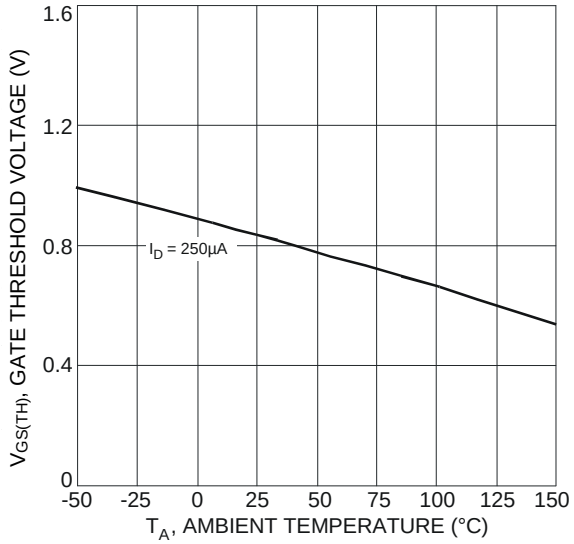


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

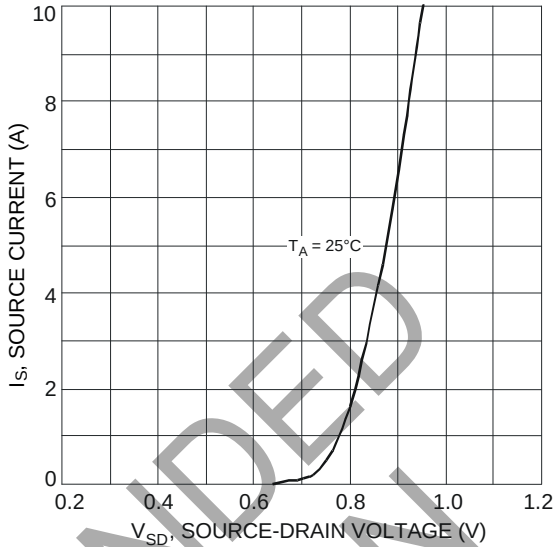


Fig. 8 Diode Forward Voltage vs. Current

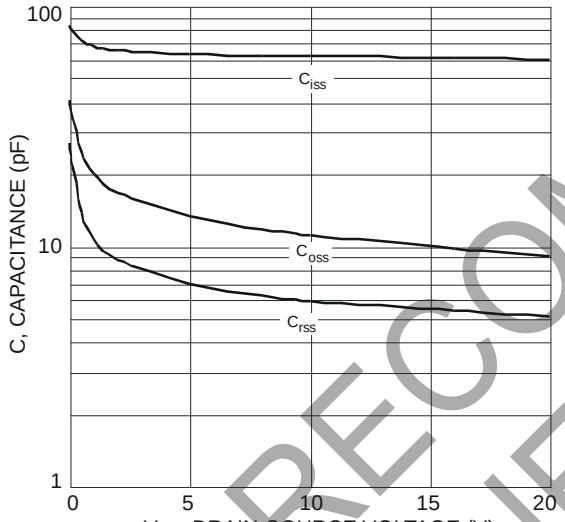


Fig. 9 Typical Capacitance

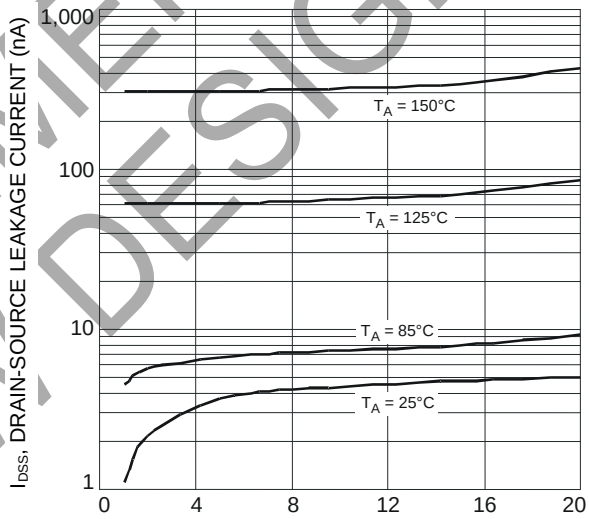
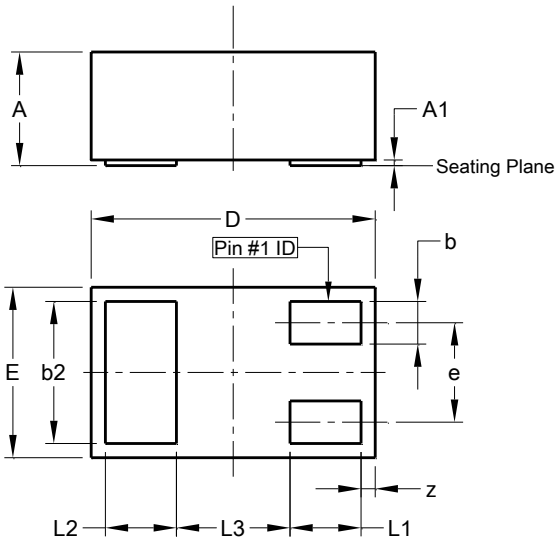


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3

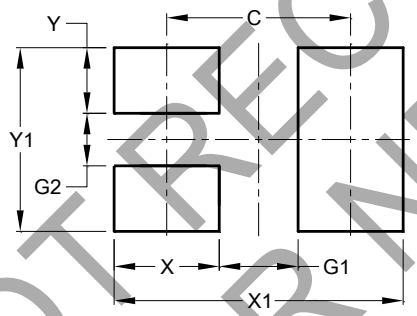


X2-DFN1006-3			
Dim	**Min**	**Max**	**Typ**
A	—	0.40	—
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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